2SD1499

Silicon NPN triple diffusion planar type

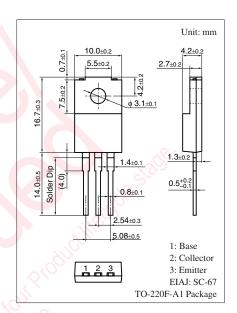
For high power amplification Complementary to 2SB1063

■ Features

- Extremely satisfactory linearity of the forward current transfer ratio h_{FE}
- Wide safe operation area
- High transition frequency f_T
- Full-pack package which can be installed to the heat sink with one screw.

■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|----------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V_{CBO} | 100 | V | |
| Collector-emitter voltage (Base open) | V_{CEO} | 100 | V | |
| Emitter-base voltage (Collector open) | V_{EBO} | 5 | V | |
| Collector current | I_{C} | 5 | A | |
| Peak collector current | I_{CP} | 8 | A | |
| Collector power | P _C | 40 | W | |
| dissipation $T_a = 25^{\circ}C$ | | 2.0 | 101 | |
| Junction temperature | T_{j} | 150 | °C | |
| Storage temperature | T_{stg} | -55 to +150 | °C C | |



■ Electrical Characteristics T_C = 25°C ± 3°C

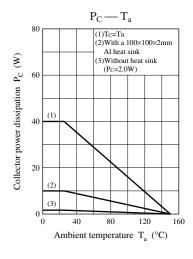
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|-----|-----|-----|------|
| Base-emitter voltage | V_{BE} | $V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$ | | 0. | 1.8 | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 100 \text{ V}, I_{E} = 0$ | 160 | | 50 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 3 \text{ V}, I_{C} = 0$ | | | 50 | μΑ |
| Forward current transfer ratio | h _{FE1} | $V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$ | 20 | | | _ |
| | h _{FE2} * | $V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$ | 40 | | 200 | |
| | h _{FE3} | $V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ A}$ | 20 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 3 \text{ A}, I_B = 0.3 \text{ A}$ | | | 2.0 | V |
| Transition frequency | f_T | $V_{CE} = 5 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$ | | 20 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 90 | | pF |
| (Common base, input open circuited) | | | | | | |

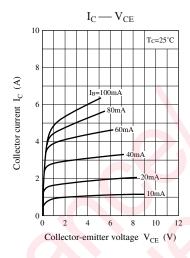
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

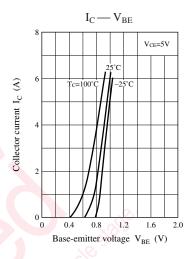
2. *: Rank classification

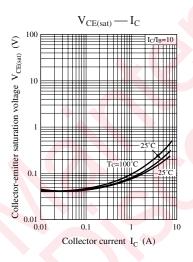
| Rank | R | Q | Р |
|------------------|----------|----------|------------|
| h _{FE2} | 40 to 80 | 60 to120 | 100 to 200 |

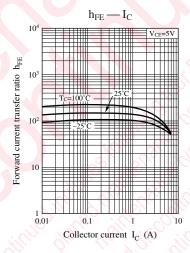
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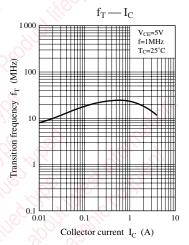


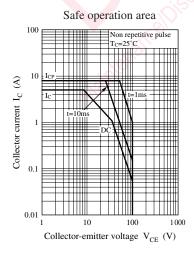


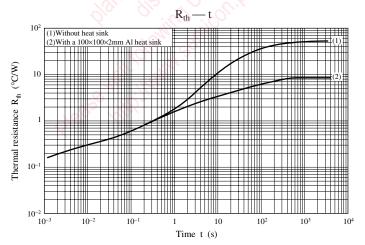












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